

Abstract of the Disclosure

A semiconductor memory device comprises a word line drive circuit including a drive transistor, which drives a word line; a circuit for turning the drive transistor OFF right after an output of the word line drive circuit reaches a high level; and a word-line-voltage increasing circuit for increasing a voltage of the word line after the drive transistor turns OFF. The word-line-voltage increasing circuit includes a coupling capacitor one end of which is connected to the word line, and a capacitor drive circuit an output end of which is connected to the other end of the coupling capacitor. The capacitor drive circuit switches its output from a low level to a high level at turn-OFF timing of the drive transistor. The coupling capacitor includes a wiring line running along the word line.